

209544US-2



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
YOUICHI ISHIMURA ET AL. : EXAMINER: TRAN, T.  
SERIAL NO: 09/881,675 :  
FILED: JUNE 18, 2001 : GROUP ART UNIT: 2811  
FOR: FIELD-EFFECT :  
SEMICONDUCTOR DEVICE :

RECEIVED  
JUL - 8 2002  
TECHNOLOGY CENTER 2800  
7/a  
FJONES  
10-24-02

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated April 10, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please add new claims 6-10 as follows:

6. (New) A field-effect semiconductor device comprising:

a semiconductor layer of a first conductivity type, wherein said semiconductor layer comprises a buffer layer of a first doping concentration and a second layer of a second doping concentration, wherein said first doping concentration is higher than said second doping concentration;

a collector region of a second conductivity type formed beneath said semiconductor layer and equipped with a collector electrode on its lower surface;

a base region of the second conductivity type formed as part of the upper surface of said semiconductor layer;